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1/1 - (C) FILE CA
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 TI - Excimer laser patterning associated with silylation and oxygen reactive ion etching
 IN - Fukui, Akiyoshi; Tokui, Akira
 PA - Mitsubishi Electric Corp., Japan
 SO - Jpn. Kokai Tokkyo Koho, 4 pp.
 CODEN: JKXXAF
 DT - Patent
 LA - Japanese
 IC - ICM G03F007/038
 ICS G03F007/36;G03F7/38;H01L21/027
 ICA - H01L021-22; H01L021-266
 CC - 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)
 Section cross-reference(s): 76

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PN	- JP3006566	A	19910114	JP 1989-141765	19890602
PR	- JP 1989-141765				19890602
AB	- In patterning of resist for manuf. of semiconductor device, a novolak formed on a substrate is selectively irradiated by excimer laser beam silylated and dry-developed by O plasma reactive ion etching. Thus, a semiconductor substrate was spin-coated with a novolak film, selective irradiated by KrF excimer laser, treated by hexamethyldisilazane in va at high temp., and dry-etched by O plasma to give a precise pattern ha rectangular section.				
ST	- patterning resist excimer laser silylation; novolak methylsilylamine silylation dry etching; oxygen plasma novolak resist etching; semiconductor device patterning excimer laser				
IT	- Semiconductor devices (patterning of resist for, excimer laser irradn. and silylation and oxygen plasma reactive ion etching in)				
IT	- Phenolic resins, uses and miscellaneous RL: USES (Uses) (novolak, excimer laser resists from, patterning of, silylation and oxygen plasma reactive ion etching in, for semiconductor device)				
IT	- Resists (photo-, patterning of, excimer laser irradn. and silylation and oxy plasma reactive ion etching in)				
IT	- 999-97-3, Hexamethyldisilazne 34478-34-7, Trimethylsilyldiamine RL: USES (Uses) (photoresist modified by, for patterning of semiconductor device by excimer laser irradn. and oxygen plasma reactive ion etching)				